SN54ABT651 . . . JT PACKAGE SN74ABT651 . . . DB, DW, NT, OR PW PACKAGE

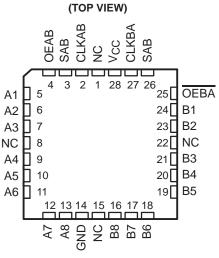
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- State-of-the-Art *EPIC-*II*B*[™] BiCMOS Design Significantly Reduces Power Dissipation
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C
- High-Drive Outputs (-32-mA I_{OH}, 64-mA I_{OL})
- Multiplexed Real-Time and Stored Data
- Inverting Data Paths
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Plastic (NT) and Ceramic (JT) DIPs

description

These devices consist of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. Output-enable (OEAB and OEBA) inputs are provided to control the transceiver functions. The select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'ABT651 devices.

(TOP	VIEW)	
CLKAB [SAB [OEAB] A1 [A2 [A3 [A3 [A5 [A6 [A7 [GND]	1 2 3 4 5 6 7 8 9 10 11 12	24 23 22 21 20 19 18 17 16 15 14 13	V _{CC} CLKBA SBA OEBA B1 B2 B3 B4 B5 B6 B7 B8
SN54ABT	051.	г л Р	ACRAGE





Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it also is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and OEBA. In this configuration, each output reinforces its input. When all the other data sources to the two sets of bus lines are at high impedance, each set remains at its last state.

To ensure the high-impedance state during power up or power down, \overline{OEBA} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver (B to A). OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver (A to B).



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description (continued)

The SN54ABT651 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74ABT651 is characterized for operation from -40°C to 85°C.

	FUNCTION TABLE													
		INPU ⁻	rs			DAT	a I/o	OPERATION OR FUNCTION						
OEAB	OEBA	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	OPERATION OR FUNCTION						
L	Н	H or L	H or L	Х	Х	Input	Input	Isolation						
L	Н	Ŷ	\uparrow	Х	Х	Input	Input	Store A and B data						
Х	Н	Ŷ	H or L	Х	Х	Input	Unspecified [†]	Store A, hold B						
н	Н	\uparrow	\uparrow	Х‡	Х	Input	Output	Store A in both registers						
L	Х	H or L	\uparrow	Х	Х	Unspecified [†]	Input	Hold A, store B						
L	L	\uparrow	\uparrow	Х	x‡	Output	Input	Store B in both registers						
L	L	Х	Х	Х	L	Output	Input	Real-time B data to A bus						
L	L	Х	H or L	Х	Н	Output	Input	Stored B data to A bus						
Н	Н	Х	Х	L	Х	Input	Output	Real-time A data to B bus						
н	Н	H or L	Х	Н	Х	Input	Output	Stored A data to B bus						
н	L	H or L	H or L	Н	Н	Output	Output	Stored A data to B bus and stored B data to A bus						

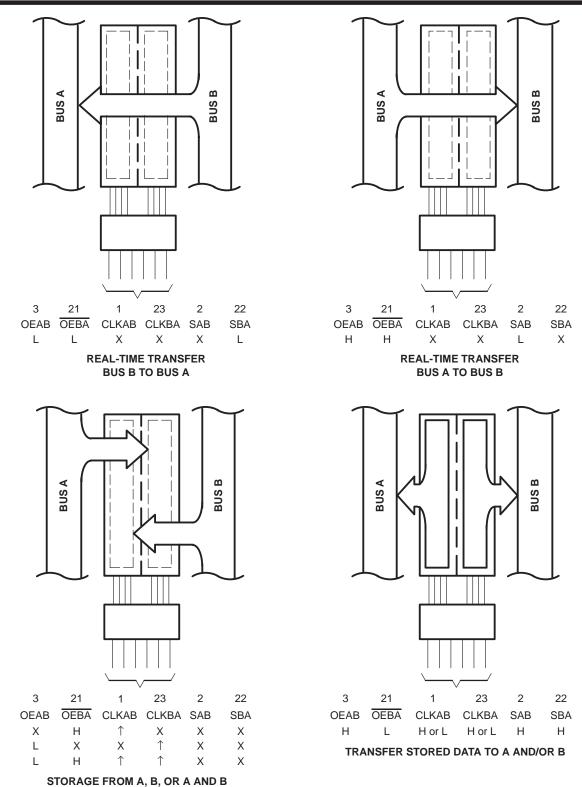
[†] The data output functions may be enabled or disabled by a variety of level combinations at OEAB or OEBA. Data input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.

[‡] When select control is low, clocks can occur simultaneously if allowances are made for propagation delays from A to B (B to A) plus setup and hold times. When select control is high, clocks must be staggered to load both registers.





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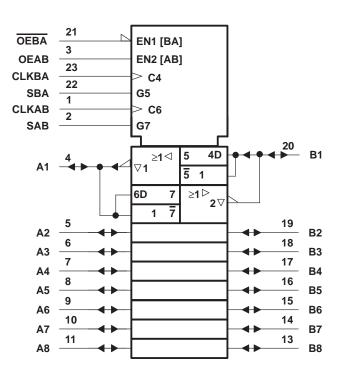
Pin numbers are for the DB, DW, JT, NT, and PW packages.

Figure 1. Bus-Management Functions



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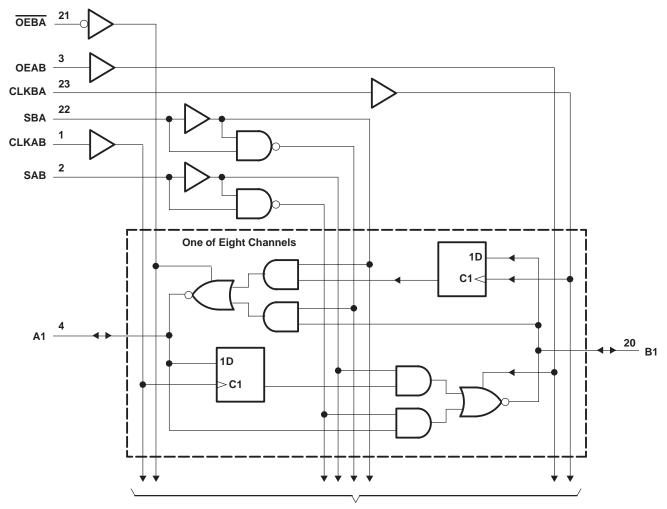
logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the DB, DW, JT, NT, and PW packages.



SN54ABT651, SN74ABT651 OCTAL BUS TRANSCEIVERS AND REGISTERS WITH 3-STATE OUTPUTS SCBS083E – JANUARY 1991 – REVISED APRIL 1998



To Seven Other Channels

Pin numbers shown are for the DB, DW, JT, NT, and PW packages.

logic diagram (positive logic)



SCBS083E - JANUARY 1991 - REVISED APRIL 1998

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V_{CC} Input voltage range, V_I (except I/O ports) (see Note 1) Voltage range applied to any output in the high or power-off state, V_O Current into any output in the low state, I_O : SN54ABT651 SN74ABT651 Input clamp current, I_{IK} ($V_I < 0$) Output clamp current, I_{OK} ($V_O < 0$) Package thermal impedance, θ_{JA} (see Note 2): DB package DW package NT package PW package	-0.5 V to 7 V -0.5 V to 5.5 V -0.5 V to 5.5 V -0.5 V to 5.5 V -0.5 W to 5.5 V -0.6 mA -128 mA -18 mA -18 mA -50 mA -50 mA -50 mA -04°C/W -067°C/W -067°C/W
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

		SN54A	BT651	SN74A	BT651	UNIT
		MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2	EW	2		V
VIL	Low-level input voltage		0.8		0.8	V
VI	Input voltage	0	Vcc	0	VCC	V
ЮН	High-level output current	C,	-24		-32	mA
IOL	Low-level output current	202	48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	32	5		5	ns/V
Т _А	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: All unused pins (control or I/O) of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



SCBS083E - JANUARY 1991 - REVISED APRIL 1998

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

DA	DAMETED	TEST CO	NDITIONS	Т	A = 25°C	;	SN54A	BT651	SN74A	BT651	UNIT	
PA	RAMETER	IESI CO	NDITIONS	MIN	TYP†	MAX	MIN	MAX	MIN	MAX	UNIT	
VIK		V _{CC} = 4.5 V,	lı = -18 mA			-1.2		-1.2		-1.2	V	
		V _{CC} = 4.5 V,	I _{OH} = –3 mA	2.5			2.5		2.5			
Veri		V _{CC} = 5 V,	I _{OH} = -3 mA	3			3		3		V	
VOH		V _{CC} = 4.5 V	I _{OH} = -24 mA	2			2				v	
		VCC = 4.5 V	I _{OH} = -32 mA	2*					2			
Vei		V _{CC} = 4.5 V	I _{OL} = 48 mA			0.55		0.55			V	
VOL		VCC = 4.5 V	I _{OL} = 64 mA			0.55*				0.55	v	
V _{hys}					100			2			mV	
L.	Control inputs	V _{CC} = 5.5 V,	$V_{I} = V_{CC}$ or GND			±1		1		±1	μA	
łı	A or B ports	VCC = 5.5 V,	VI = VCC OL GIND			±100		±100		±100	μΑ	
IOZH‡		V _{CC} = 5.5 V,	V _O = 2.7 V			50	4	50		50	μΑ	
IOZL [‡]		V _{CC} = 5.5 V,	$V_{O} = 0.5 V$			-50	20	-50		-50	μΑ	
loff		$V_{CC} = 0,$	VI or VO ≤ 4.5 V			±100	90			±100	μΑ	
ICEX		V _{CC} = 5.5 V, V _O = 5.5 V	Outputs high			50	49	50		50	μA	
IO§		V _{CC} = 5.5 V,	V _O = 2.5 V	-50	-100	-180	-50	-180	-50	-180	mA	
		V _{CC} = 5.5 V,	Outputs high			250		250		250	μA	
ICC		$I_{O} = 0,$	Outputs low			30		30		30	mA	
		$V_I = V_{CC}$ or GND	Outputs disabled			250		250		250	μA	
∆ICC¶		$V_{CC} = 5.5 V$, One inp Other inputs at V_{CC} of				1.5		1.5		1.5	mA	
Ci	Control inputs	VI = 2.5 V or 0.5 V			6						pF	
Cio	A or B ports	V _O = 2.5 V or 0.5 V			7.5						pF	

* On products compliant to MIL-PRF-38535, this parameter does not apply.

[†] All typical values are at $V_{CC} = 5$ V.

[‡] The parameters I_{OZH} and I_{OZL} include the input leakage current.

§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

 ¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 2)

		V _{CC} T _A =	= 5 V, 25°C	SN54A	BT651	SN74A	BT651	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency		125		125		125	MHz
tw	Pulse duration, CLK high or low	4		4	N.M	4		ns
t _{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	3		~ 3		3		ns
t _h	Hold time, A or B after CLKAB \uparrow or CLKBA \uparrow	0		0		0		ns



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 2)

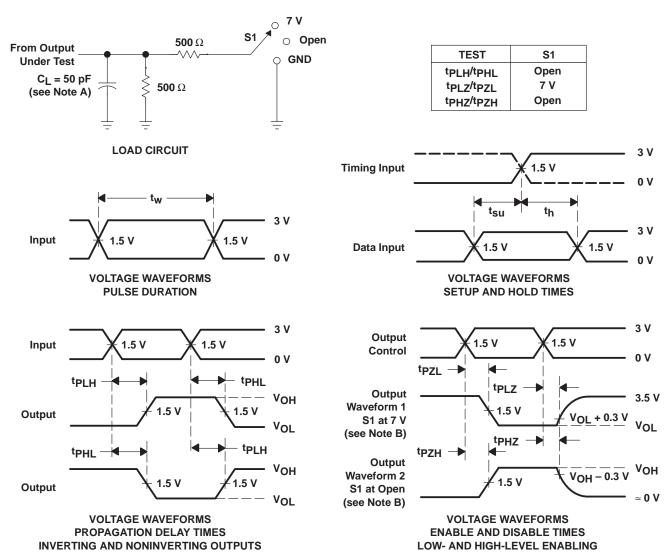
PARAMETER	FROM (INPUT)	TO (OUTPUT)		V _{CC} = 5 V, T _A = 25°C			BT651	SN74A	UNIT	
		(001201)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f _{max}			125			125		125		MHz
^t PLH	CLKBA or CLKAB	A or B	2.2	4	5.1	2.2	5.9	2.2	5.6	ns
^t PHL	CLKBA UI CLKAB	AUB	1.7	4	5.1	1.7	5.9	1.7	5.6	115
^t PLH	A or B	B or A	1.5	4	5.1	1.5	6.4	1.5	6.2	ns
^t PHL	AUB	B of A	1.5	3.3	4.6	1.5	5.6	1.5	5.4	115
^t PLH	SAB or SBA [†]	A or B	1.5	4	5.1	1.5	6.8	1.5	6.5	ns
^t PHL	SAB OF SBAT		1.5	3.6	4.9	1.5	6.2	1.5	5.9	113
^t PZH		А	1.3	3.6	4.6	1.3	5.9	1.3	5.8	ns
tPZL	OEBA	A	2.5	5.7	6.8	2.5	8.9	2.5	8.5	115
^t PHZ	OEBA	А	1.5	3.2	4.5	9.5	6.2	1.5	5	ns
^t PLZ	OEBA	~	1.5	3	3.8	Q 1.5	4.3	1.5	4.1	115
^t PZH	OEAB	В	1.8	4.3	6.1	1.8	6.7	1.8	6.5	ns
^t PZL		0	2.9	5.5	6.5	2.9	7.6	2.9	7.4	115
^t PHZ	OEAB	В	1.5	3.3	4.5	1.5	6.5	1.5	5.5	ns
^t PLZ		0	1.5	3.4	4.4	1.5	5.2	1.5	5.1	115

[†] These parameters are measured with the internal output state of the storage register opposite that of the bus input.

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SCBS083E - JANUARY 1991 - REVISED APRIL 1998



PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , t_f \leq 2.5 ns, t_f \leq 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74ABT651DW	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651	Samples
SN74ABT651DWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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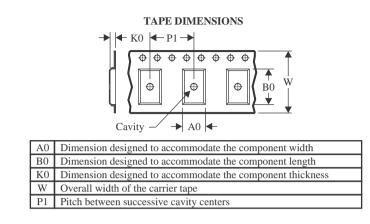


TEXAS

NSTRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	· ·	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ABT651DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1



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PACKAGE MATERIALS INFORMATION

5-Dec-2023



*All dimensions are nominal

Device	Package Type	pe Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74ABT651DWR	SOIC	DW	24	2000	350.0	350.0	43.0	

TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN74ABT651DW	DW	SOIC	24	25	506.98	12.7	4826	6.6

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